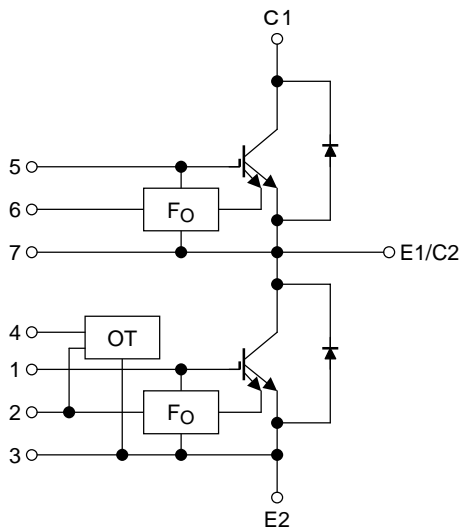


MG200Q2YS60A(1200V/200A 2in1)

High Power Switching Applications
 Motor Control Applications

- Integrates a complete half bridge power circuit and fault-signal output circuit in one package.
 (short circuit and over temperature)
- The electrodes are isolated from case.
- Low thermal resistance
- $V_{CE(sat)} = 2.4\text{ V (typ.)}$

Equivalent Circuit

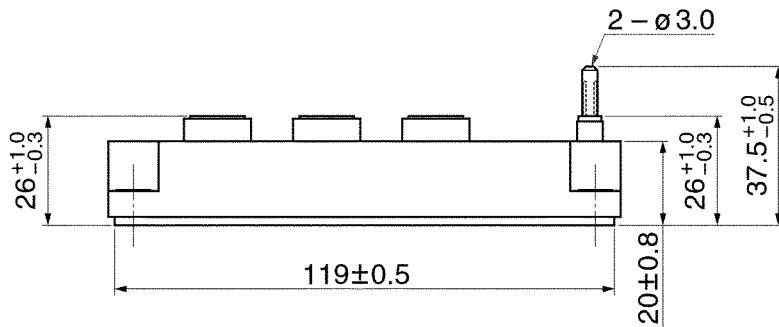
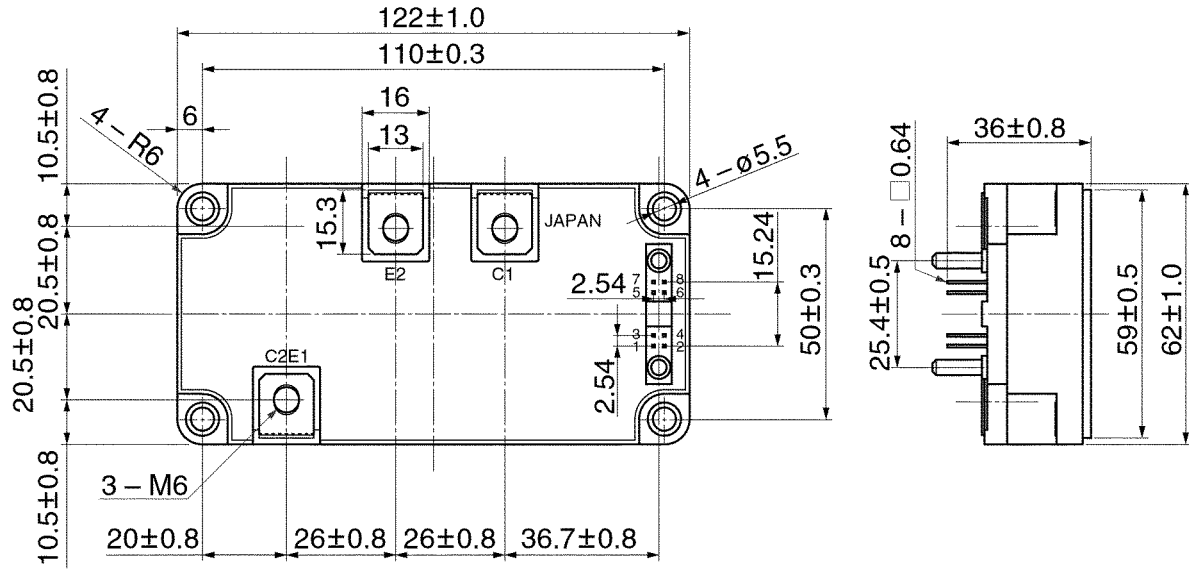


Signal terminal

1.	G (L)	2.	F _O (L)	3.	E (L)	4.	V _D
5.	G (H)	6.	F _O (H)	7.	E (H)	8.	Open

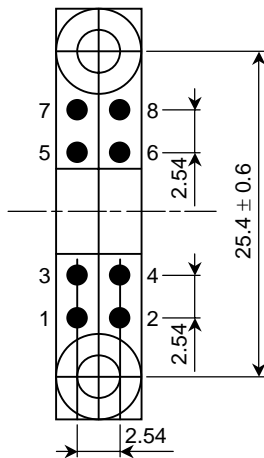
Package Dimensions: 2-123C1B

Unit: mm



- | | | | | | | | |
|----|-------|----|--------------------|----|-------|----|----------------|
| 1. | G (L) | 2. | F _O (L) | 3. | E (L) | 4. | V _D |
| 5. | G (H) | 6. | F _O (H) | 7. | E (H) | 8. | Open |

Signal Terminal Layout



- | | | | | | | | |
|----|-------|----|--------------------|----|-------|----|----------------|
| 1. | G (L) | 2. | F _O (L) | 3. | E (L) | 4. | V _D |
| 5. | G (H) | 6. | F _O (H) | 7. | E (H) | 8. | Open |

Weight: 375 g

Maximum Ratings (Ta = 25°C)

Stage	Characteristics	Symbol	Rating	Unit	
Inverter	Collector-emitter voltage	V_{CES}	1200	V	
	Gate-emitter voltage	V_{GES}	±20	V	
	Collector current	DC	I_C	200	A
		1 ms	I_{CP}	400	
	Forward current	DC	I_F	200	A
		1 ms	I_{FM}	400	
Collector power dissipation (Tc = 25°C)		P_C	2000	W	
Control	Control voltage (OT)	V_D	20	V	
	Fault input voltage	V_{FO}	20	V	
	Fault input current	I_{FO}	20	mA	
Module	Junction temperature	T_j	150	°C	
	Storage temperature range	T_{stg}	-40~125	°C	
	Operation temperature range	T_{ope}	-20~100	°C	
	Isolation voltage	V_{isol}	2500 (AC 1 min)	V	
	Screw torque	—	3 (M5)	N·m	

Electrical Characteristics (Tj = 25°C)

1. Inverter Stage

Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit			
Gate leakage current	I_{GES}	$V_{GE} = \pm 20\text{ V}, V_{CE} = 0$	—	—	+3/-4	mA			
		$V_{GE} = +10\text{ V}, V_{CE} = 0$	—	—	100	nA			
Collector cut-off current	I_{CES}	$V_{CE} = 1200\text{ V}, V_{GE} = 0$	—	—	1.0	mA			
Gate-emitter cut-off voltage	$V_{GE}(\text{off})$	$V_{CE} = 5\text{ V}, I_C = 200\text{ mA}$	6.0	7.0	8.0	V			
Collector-emitter saturation voltage	$V_{CE}(\text{sat})$	$V_{GE} = 15\text{ V}, I_C = 200\text{ A}$	Tj = 25°C	—	2.4	2.8	V		
			Tj = 125°C	—	—	3.2			
Input capacitance	C_{ies}	$V_{CE} = 10\text{ V}, V_{GE} = 0, f = 1\text{ MHz}$	—	15000	—	pF			
Switching time	Turn-on delay time	$V_{CC} = 600\text{ V}, I_C = 200\text{ A}$ $V_{GE} = \pm 15\text{ V}, R_G = 10\ \Omega$ (Note 1)	0.10	—	1.00	μs			
	Turn-off time						—	—	2.00
	Fall time						—	—	0.50
Reverse recovery time	t_{rr}		—	—	0.50				
Forward voltage	V_F	$I_F = 200\text{ A}$	—	2.4	2.8	V			

Note 1: Switching time test circuit & timing chart

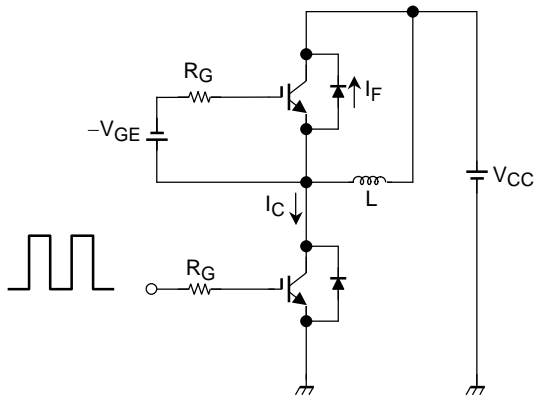
2. Control (Tc = 25°C)

Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit
Fault output current	OC	$V_{GE} = 15\text{ V}$	240	—	—	A
Over temperature	OT	—	100	—	125	°C
Fault output delay time	$t_d(F_o)$	$V_{CC} = 600\text{ V}, V_{GE} = \pm 15\text{ V}$	—	—	8	μs

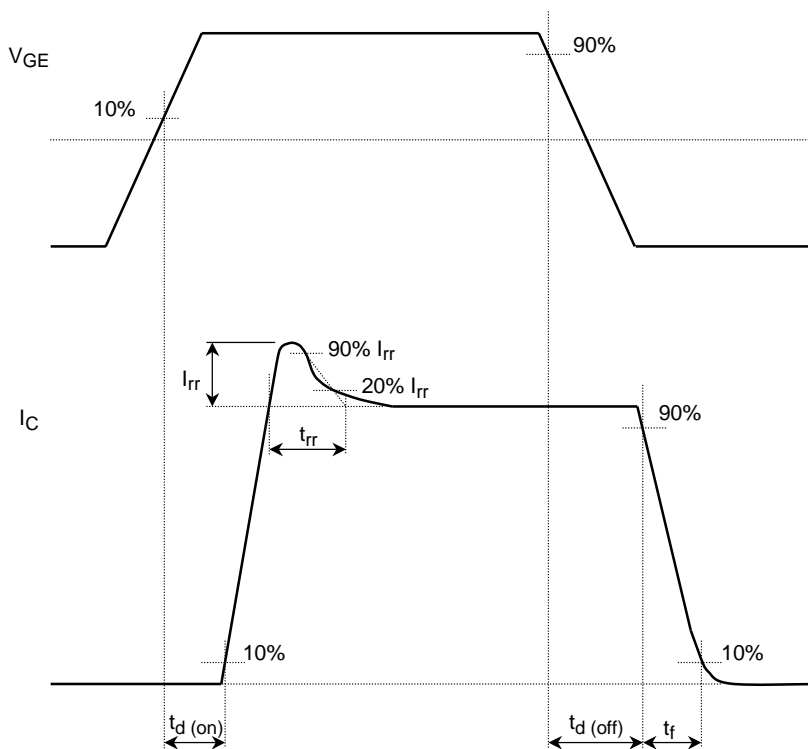
3. Module (Tc = 25°C)

Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit
Junction to case thermal resistance	$R_{th(j-c)}$	Inverter IGBT stage	—	—	0.062	°C/W
		Inverter FRD stage	—	—	0.136	
Case to fin thermal resistance	$R_{th(c-f)}$	With silicon compound	—	0.013	—	°C/W

Switching Time Test Circuit



Timing Chart



Remark**<Short circuit capability condition>**

- Short circuit capability is 6 μ s after fault output signal.
Please keep following condition to use fault output signal.
 - $V_{CC} \leq 750$ V
 - 14.8 V $\leq V_{GE} \leq 17.0$ V
 - $R_G \geq 10$ Ω
 - $T_j \leq 125^\circ$ C

<Gate voltage>

- To use this product, V_{GE} must be provided higher than 14.8 V.
In case V_{GE} is less than 14.8 V, fault signal FO may not be output even under error conditions.

